



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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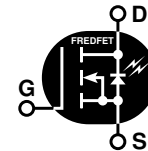


### POWER MOS V®

**FREDFET**


Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.

- Fast Recovery Body Diode
- Lower Leakage
- Faster Switching
- 100% Avalanche Tested
- Popular SOT-227 Package



#### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT30M40JVFR	UNIT
$V_{DSS}$	Drain-Source Voltage	300	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	70	Amps
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	280	
$V_{GS}$	Gate-Source Voltage Continuous	$\pm 30$	Volts
$V_{GSM}$	Gate-Source Voltage Transient	$\pm 40$	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	450	Watts
	Linear Derating Factor	3.6	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300	
$I_{AR}$	Avalanche Current <sup>①</sup> (Repetitive and Non-Repetitive)	70	Amps
$E_{AR}$	Repetitive Avalanche Energy <sup>①</sup>	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy <sup>④</sup>	2500	

#### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu\text{A}$ )	300			Volts
$I_{D(on)}$	On State Drain Current <sup>②</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ )	70			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10V, 0.5 I_{D[Cont.]}$ )			0.040	Ohms
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = V_{DSS}, V_{GS} = 0V$ )			250	$\mu\text{A}$
	Zero Gate Voltage Drain Current ( $V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )			1000	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 2.5\text{mA}$ )	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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**DYNAMIC CHARACTERISTICS**

**APT30M40JVFR**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V		8500	10200	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25V		1500	2100	
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1 MHz		390	585	
Q <sub>g</sub>	Total Gate Charge ③	V <sub>GS</sub> = 10V		285	425	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DD</sub> = 0.5 V <sub>DSS</sub>		56	85	
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	I <sub>D</sub> = I <sub>D</sub> [Cont.] @ 25°C		120	180	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> = 15V		16	32	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 0.5 V <sub>DSS</sub>		20	40	
t <sub>d(off)</sub>	Turn-off Delay Time	I <sub>D</sub> = I <sub>D</sub> [Cont.] @ 25°C		48	72	
t <sub>f</sub>	Fall Time	R <sub>G</sub> = 0.6Ω		4	8	

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I <sub>S</sub>	Continuous Source Current (Body Diode)			70	Amps
I <sub>SM</sub>	Pulsed Source Current ① (Body Diode)			280	
V <sub>SD</sub>	Diode Forward Voltage ② (V <sub>GS</sub> = 0V, I <sub>S</sub> = -I <sub>D</sub> [Cont.])			1.3	Volts
dv/dt	Peak Diode Recovery dv/dt ⑤			5	V/ns
t <sub>rr</sub>	Reverse Recovery Time (I <sub>S</sub> = -I <sub>D</sub> [Cont.], di/dt = 100A/μs)	T <sub>j</sub> = 25°C		240	ns
		T <sub>j</sub> = 125°C		500	
Q <sub>rr</sub>	Reverse Recovery Charge (I <sub>S</sub> = -I <sub>D</sub> [Cont.], di/dt = 100A/μs)	T <sub>j</sub> = 25°C	1.1		μC
		T <sub>j</sub> = 125°C	5.2		
I <sub>RRM</sub>	Peak Recovery Current (I <sub>S</sub> = -I <sub>D</sub> [Cont.], di/dt = 100A/μs)	T <sub>j</sub> = 25°C	12		Amps
		T <sub>j</sub> = 125°C	22		

**THERMAL / PACKAGE CHARACTERISTICS**

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R <sub>θJC</sub>	Junction to Case			0.28	°C/W
R <sub>θJA</sub>	Junction to Ambient			40	
V <sub>Isolation</sub>	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations.			13	lb·in

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%
- ③ See MIL-STD-750 Method 3471
- ④ Starting T<sub>j</sub> = +25°C, L = 1.02mH, R<sub>G</sub> = 25Ω, Peak I<sub>L</sub> = 70A
- ⑤ I<sub>S</sub> ≤ -I<sub>D</sub> [Cont.], di/dt = 100A/μs, V<sub>DD</sub> ≤ V<sub>DSS</sub>, T<sub>j</sub> ≤ 150°C, R<sub>G</sub> = 2.0Ω, V<sub>R</sub> = 200V

APT Reserves the right to change, without notice, the specifications and information contained herein.

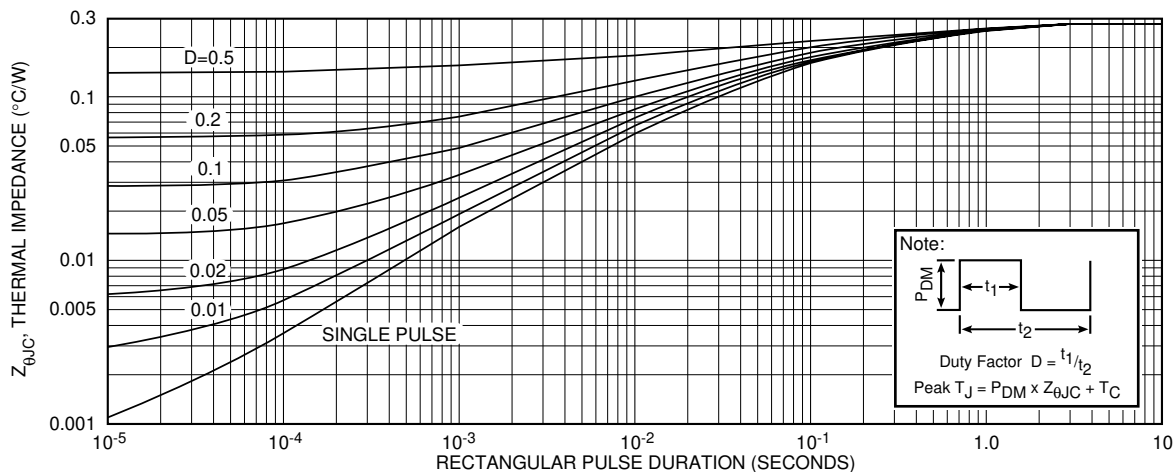
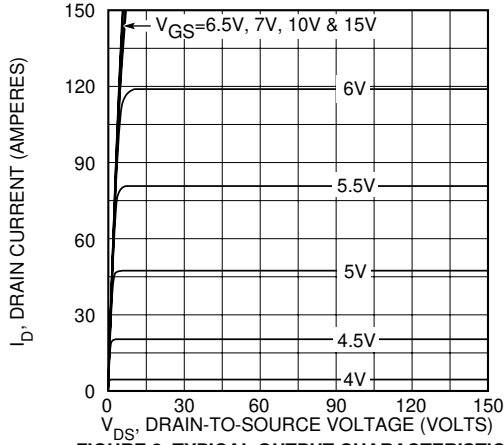
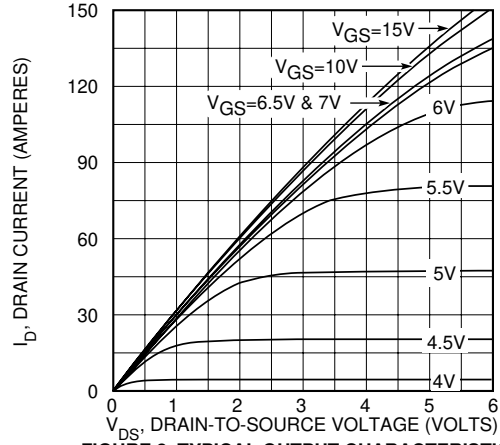


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

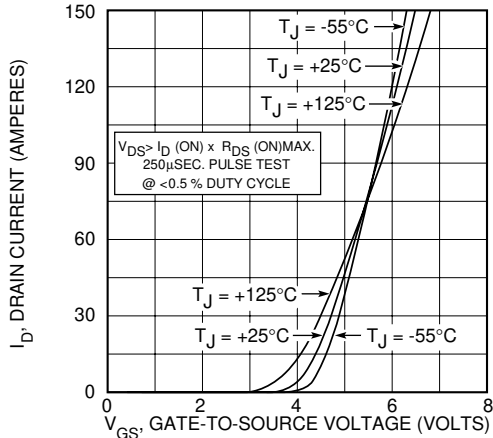
**APT30M40JVFR**



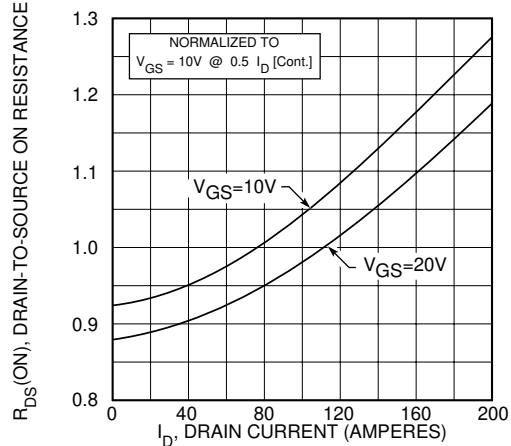
**FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS**



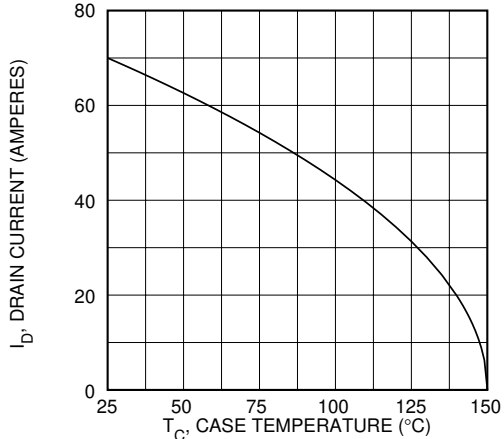
**FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS**



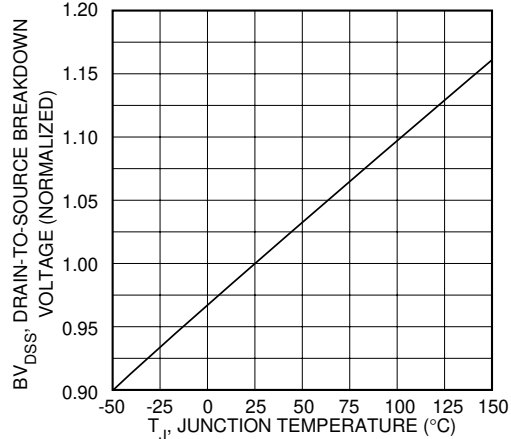
**FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS**



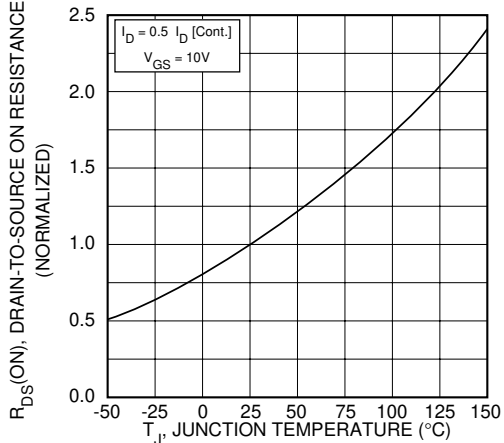
**FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT**



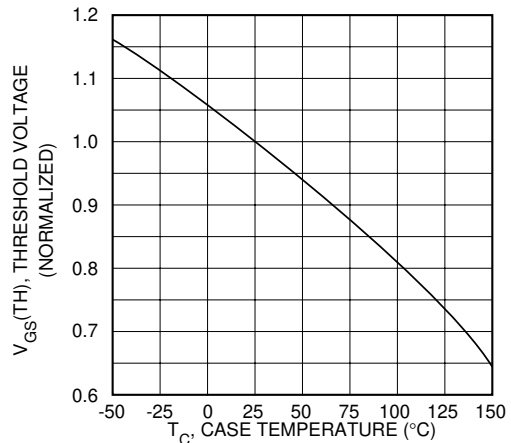
**FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE**



**FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE**



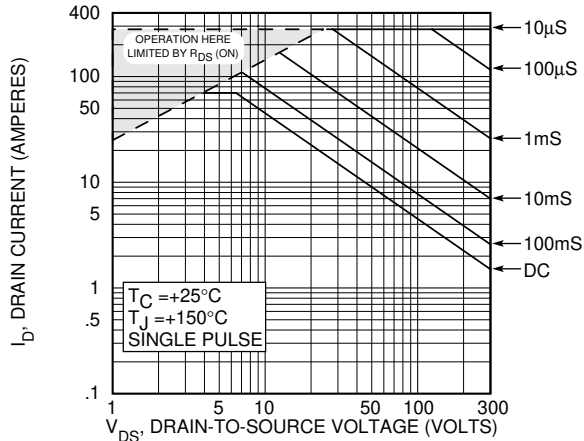
**FIGURE 8, ON-RESISTANCE vs. TEMPERATURE**



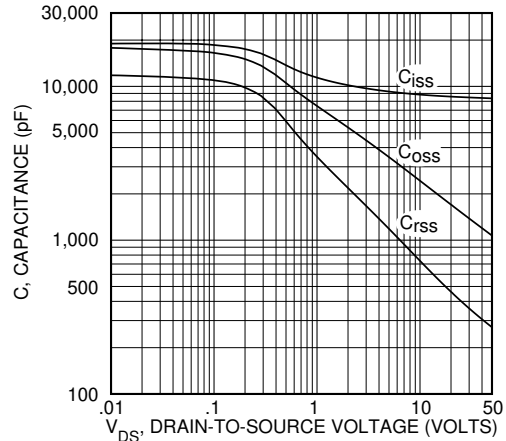
**FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE**



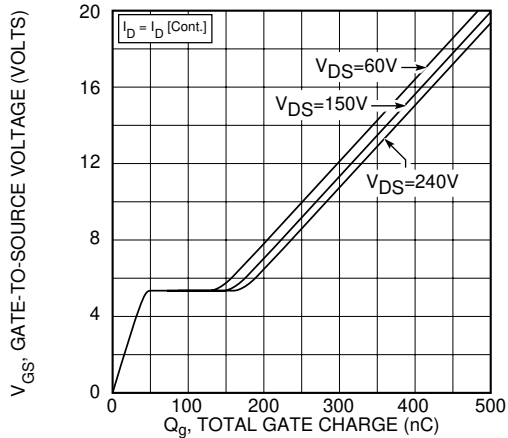
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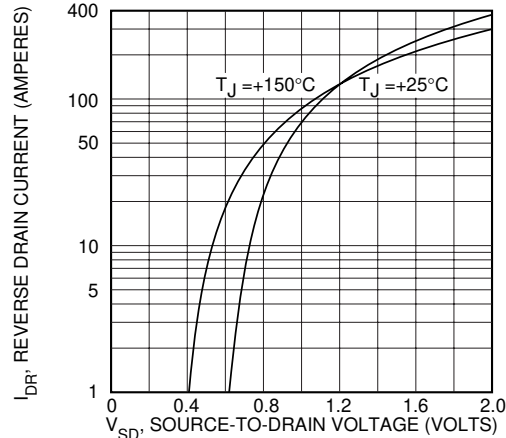
**FIGURE 10, MAXIMUM SAFE OPERATING AREA**



**FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE**

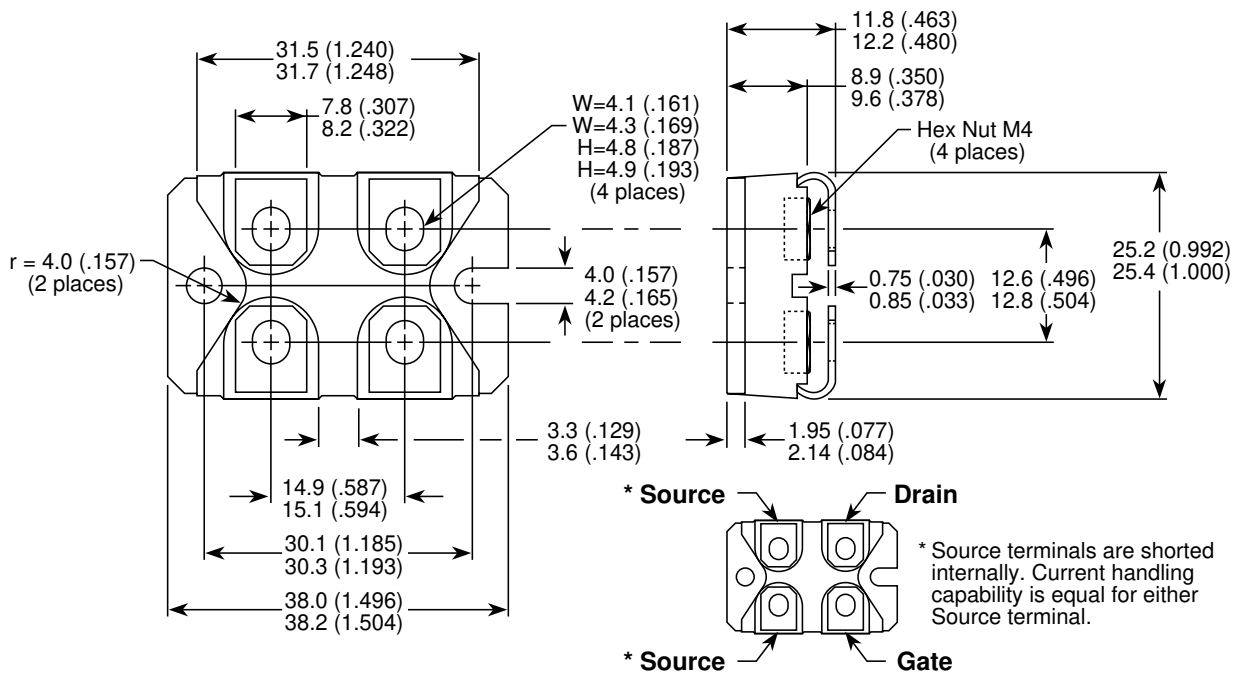


**FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE**



**FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE**

**SOT-227 (ISOTOP®) Package Outline**



Dimensions in Millimeters and (Inches)